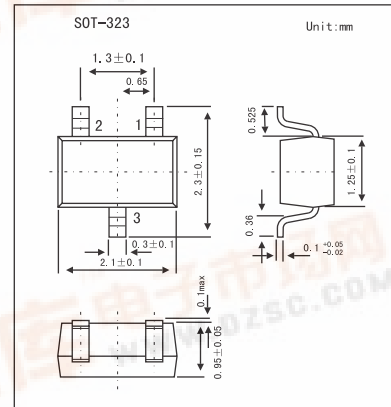


SMD Type Diodes

Silicon Schottky Barrier Diode
HSB276S

Features

- High forward current, Low capacitance.
- HSB276S which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.



Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	3	V
Average rectified current	I _o	30	m A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 1.0 mA	3			V
Reverse current	I _R	V _R = 0.5 V			50	μ A
Forward current	I _F	V _F = 0.5 V	35			mA
Capacitance	C	V _R = 0.5 V, f = 1 MHz			0.90	pF
Capacitance deviation	ΔC	V _R = 0.5V, f = 1 MHz			0.10	pF
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; I_R ≥ 100 μ A at V_R = 0.5 V

Marking

Marking	C2
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